

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 37.60MM×19.00MM OUTLINE
- ✧ THREE DIGIT
- ✧ MONO COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

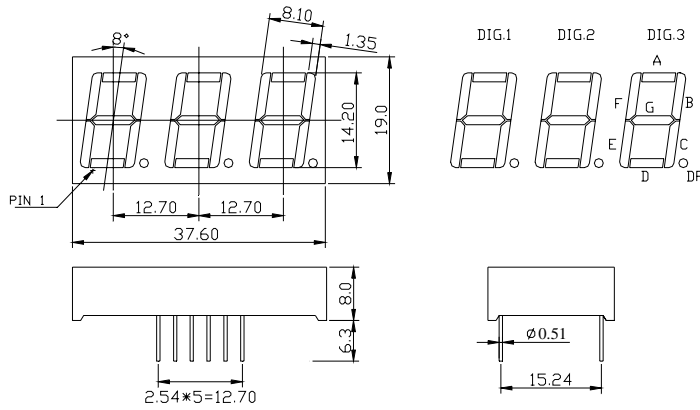
The REC-S5361CSR/ASR is a 0.56 inches (14.20mm) digit height, 37.60mm×19.0mm outline, single color, three digits numeric display. This display utilizes super-red LED chips fabricated from GaAlAs epiwafer on GaAs substrate grown by liquid phase epitaxy. These devices have black face and white segments.

DEVICE

PART NO.	EMITTING COLOR	DESCRIPTION
REC-S5361CSR/ASR	Super-Red	Common Cathode,Black Face & White Seg.

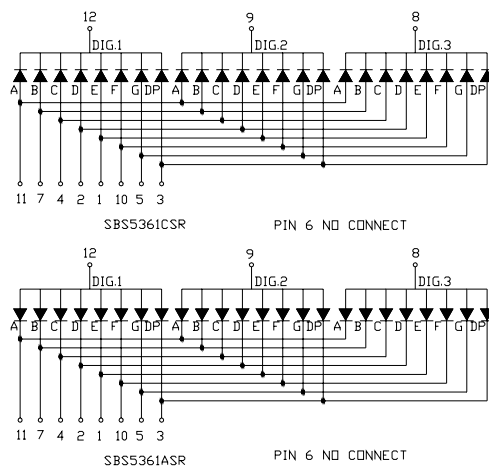
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PACKAGE DIMENSION



Notes: 1.All dimension are in millimeters.
2.Tolerance is ± 0.25 mm unless otherwise specified.

INTERNAL CIRCUIT DIAGRAM



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PIN CONNECTION

PIN NO.	CONNECTION		PIN NO.	CONNECTION	
	SBS5361CSR	SBS5361ASR		SBS5361CSR	SBS5361ASR
1	Anode E	Cathode E	7	Anode B	Cathode E
2	Anode D	Cathode D	8	Cathode Dig. 3	Anode Dig. 3
3	Anode DP	Cathode DP	9	Cathode Dig. 2	Anode Dig. 2
4	Anode C	Cathode C	10	Anode F	Cathode F
5	Anode G	Cathode G	11	Anode A	Cathode A
6	No Connect	No Connect	12	Cathode Dig. 1	Anode Dig. 1

ABSOLUTE MAXIMUM RATING AT $T_A=25^{\circ}\text{C}$

PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per Seg.	P_{AD}	60	mW
Peak Forward Current per Seg.	I_{PF}	80	mA
Continuous Forward Current per Seg.	I_{AF}	20	mA
Reverse Voltage per Seg.	V_R	5	V
Operating Temperature Range, T_{opr}		- 25° C to + 60° C	
Storage Temperature Range, T_{stg}		- 30° C to + 85° C	
Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C			

ELECTRO – OPTICAL CHARACTERISTICS AT $T_A=25^{\circ}\text{C}$

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per Seg., I_V ($I_F=20\text{mA}$)	mcd	7	10	12
Peak Emission Wavelength, λ_P ($I_F=20\text{mA}$)	nm		640	
Special Line Half-Width, $\Delta\lambda$ ($I_F=20\text{mA}$)	nm		20	
Forward Voltage per Seg., V_F ($I_F=20\text{mA}$)	V	1.6	1.8	2.1
Reverse Current per chipSeg., I_R , ($V_R=5\text{V}$)	μA			100
Luminous Intensity Matching Ratio, I_{V-m} ($I_F=20\text{mA}$)				2:1